

# N-channel 60 V 2 mΩ standard level MOSFET in D2PAK Rev. 2 — 29 February 2012 Product dat

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### 1.3 Applications

. .

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data			_		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	60	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	<u>[1]</u> _	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	306	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	1.66	2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 13</u> ;see <u>Figure 12</u>	-	2.66	3.1	mΩ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 75 A; $V_{DS}$ = 30 V;	-	32	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14;see Figure 15	-	137	-	nC
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$      V_{GS} = 10 \text{ V};  \text{T}_{j(init)} = 25 \text{ °C};  \text{I}_{\text{D}} = 120 \text{ A}; \\       V_{sup} \leq 60 \text{ V};  \text{R}_{\text{GS}} = 50  \Omega; \text{ Unclamped} $	-	-	913	mJ

[1] Continuous current is limited by package.

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#### N-channel 60 V 2 mΩ standard level MOSFET in D2PAK

### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R7-60BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

### 4. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

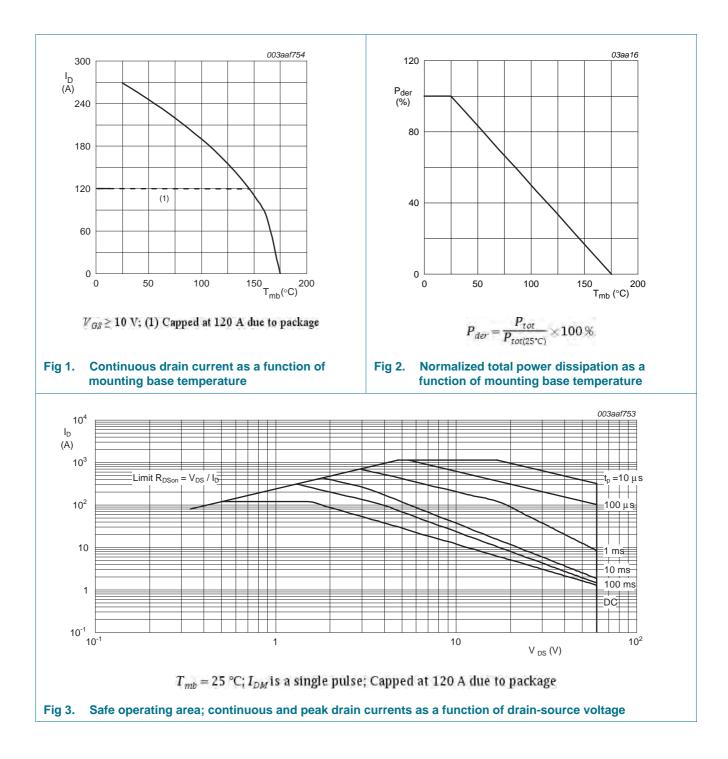
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	60	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	120	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	1076	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	306	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-di	rain diode				
ls	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u> -	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	1076	А
Avalanch	e ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup} \le 60$ V; $R_{GS}$ = 50 $\Omega$ ; Unclamped	-	913	mJ

[1] Continuous current is limited by package.

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# PSMN1R7-60BS

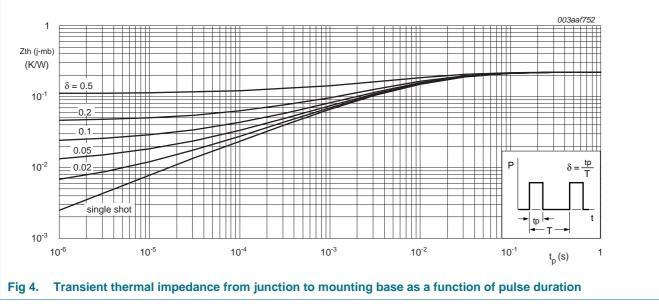
#### N-channel 60 V 2 m $\Omega$ standard level MOSFET in D2PAK



N-channel 60 V 2 mΩ standard level MOSFET in D2PAK

#### **Thermal characteristics** 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



#### N-channel 60 V 2 mΩ standard level MOSFET in D2PAK

### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 $\mu A; V_{GS}$ = 0 V; $T_j$ = -55 °C	54	-	-	V
	breakdown voltage	$I_D$ = 250 $\mu A; \ V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	10	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	1.66	2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	3.82	4.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 13</u> ; see <u>Figure 12</u>	-	2.66	3.1	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 75 A; $V_{DS}$ = 30 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	137	-	nC
		$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	129	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	48	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	29	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	19	-	nC
Q <sub>GD</sub>	gate-drain charge		-	32	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 30 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	5.7	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C;	-	9997	-	pF
C <sub>oss</sub>	output capacitance	see Figure 16	-	1210	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	594	-	рF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 0.4 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	42	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ I_D = 75 \ A$	-	56	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	115	-	ns
t <sub>f</sub>	fall time		-	49	-	ns

Symbol

# **PSMN1R7-60BS**

Тур

Max Unit

#### N-channel 60 V 2 mΩ standard level MOSFET in D2PAK

Min

ource-dra	ain diode							
SD	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; \text{ T}$ see <u>Figure 17</u>	<sub>j</sub> = 25 °C;	-	- 0.	.8	1.2	V
r	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 V <sub>DS</sub> = 30 V	) A/ $\mu$ s; V <sub>GS</sub> = 0 V;		- 57	7	-	ns
Q <sub>r</sub> recovered charge		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ V}$ $V_{DS} = 30 \text{ V}$	) A/µs; V <sub>GS</sub> = 0 V;	-	- 80	0	-	nC
250 g <sub>fs</sub> (S) 200		003aaf742	80 I <sub>D</sub> (A) 60			003	Baaf743	
100			40					
50			20	T <sub>j</sub> = 175 °C		= 25 °	∘C	
-								
0	$T_{j} = 25 \text{ °C}; V_{DS} =$	90 <sub>I<sub>D</sub>(A)</sub> 120 30V	0	2	4	V <sub>GS</sub> (	V) 6	
0 Fig 5. F		30V e as a function of es	0 Fig 6. Transfe	2 r characterist n of gate-sour	ics: drai	n cu ge; t	irrent a	
0 Fig 5. F	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductanc	30V e as a function of es	0 Fig 6. Transfe	r characterist	ics: drai	n cu ge; t	arrent ( aypical)	
<sup>6</sup> Fig 5. Fi du 10 <sup>5</sup>	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductanc	30V e as a function of es	0 Fig 6. Transfer function	r characterist of gate-sour	ics: drai	n cu ge; t	irrent a	
<sup>105</sup> C (PF)	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductanc	30V e as a function of es	0 Fig 6. Transfer function	r characterist of gate-sour	ics: drai	n cu ge; t	3aad674	
<sup>105</sup> C (pF) 10 <sup>4</sup>	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductance rain current; typical valu	30V e as a function of es	0 Fig 6. Transfe function	r characterist of gate-sour	ics: drai	n cu ge; t	3aad674	
Fig 5. Fi du 10 <sup>5</sup> C (pF) 10 <sup>4</sup> 10 <sup>3</sup>	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductance rain current; typical valu	30V e as a function of b 003aaf746 $C_{iss}$ $C_{rss}$	0 Fig 6. Transfe function (A) 150 100 50 0	r characterist	ve	n cu ge; t 003	<pre>v) irrent a typical 3aad674 4.5 = 4 </pre>	

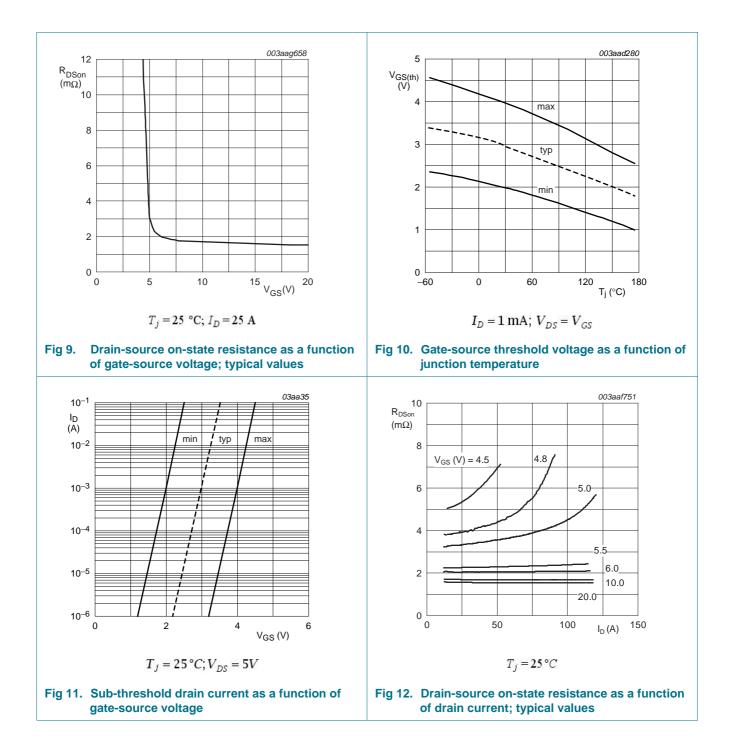
#### Characteristics ... continued Table 6. Parameter

Conditions

Product data sheet

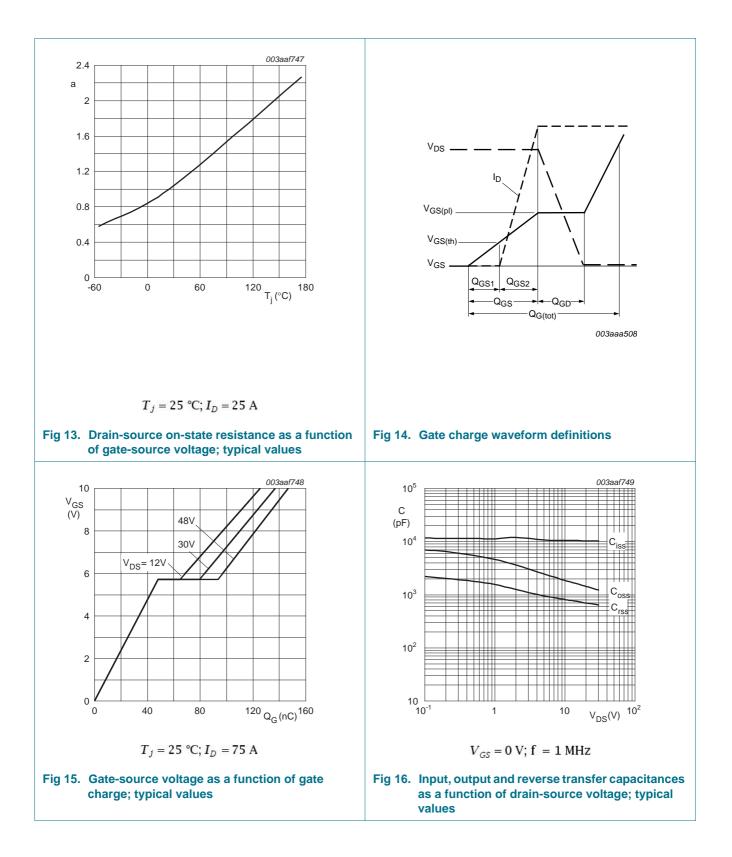
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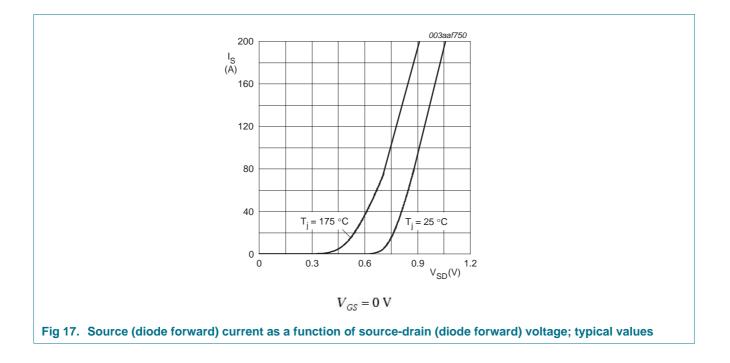
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#### N-channel 60 V 2 m $\Omega$ standard level MOSFET in D2PAK



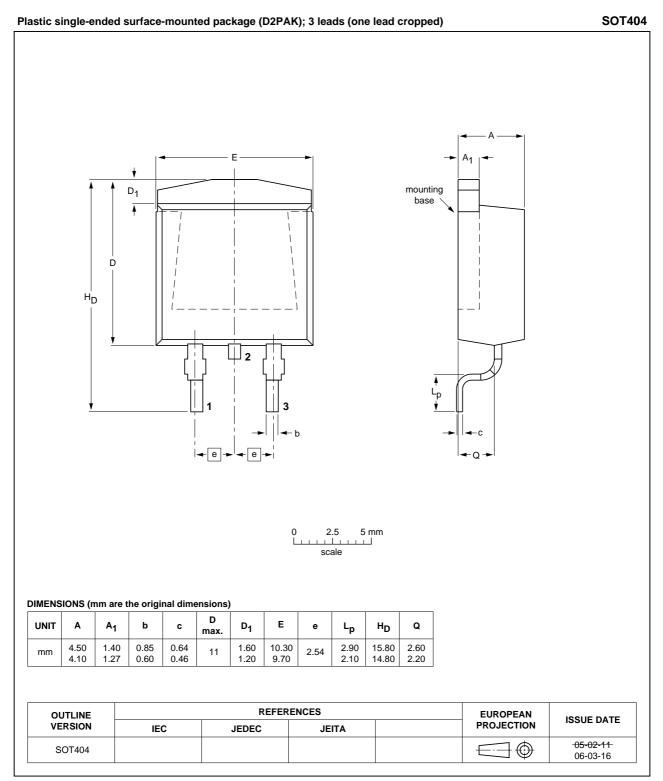
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#### N-channel 60 V 2 mΩ standard level MOSFET in D2PAK



#### N-channel 60 V 2 mΩ standard level MOSFET in D2PAK

### 7. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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#### N-channel 60 V 2 mΩ standard level MOSFET in D2PAK

### 8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R7-60BS v.2	20120229	Product data sheet	-	PSMN1R7-60BS v.1
Modifications:	<ul> <li>Status change</li> </ul>	d from objective to product.		
	<ul> <li>Various chang</li> </ul>	es to content.		
PSMN1R7-60BS v.1	20110823	Objective data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### N-channel 60 V 2 m $\Omega$ standard level MOSFET in D2PAK

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